

# N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ )(TYP.)	I <sub>D</sub> (A) <sup>a</sup>			
20	5.8 at $V_{GS} = 4.5 \text{ V}$	25			
	6.9 at V <sub>GS</sub> = 2.5 V	20			

#### **FEATURES**

DT-Trench Power MOSFET



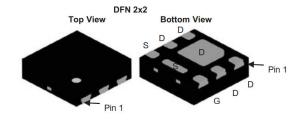
Common Drain

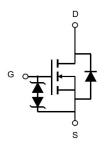


ROHS

#### **APPLICATIONS**

· 1-2 Cell Battery Protection Circuitry





Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20	V	
Gate-Source Voltage		V <sub>GS</sub>	± 12	v	
	T <sub>C</sub> = 25 °C		25 <sup>a</sup>		
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C	l_	20 <sup>a</sup>		
Continuous Diam Current (1) = 130 °C)	T <sub>A</sub> = 25 °C	l <sub>D</sub>	18 <sup>a, b, c</sup>		
	T <sub>A</sub> = 70 °C		15.1 <sup>b, c</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	75	٦	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C		12 <sup>a</sup>		
	T <sub>A</sub> = 25 °C	I <sub>S</sub>	2.9 <sup>b, c</sup>		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		24.2		
	T <sub>C</sub> = 70 °C	P <sub>D</sub>	16.3	w	
	T <sub>A</sub> = 25 °C	1 ' 1	3.5 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	Ī	2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	] 0,00	

#### Notes:

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. The DFN2X2 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80  $^{\circ}\text{C/W}.$





Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					·	<u> </u>	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA		24		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η = 250 μΑ		- 5.6			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_{D} = 250 \mu A$	0.5		1.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 5	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1		
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$				Α	
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7 A		5.8	7.3	mΩ	
	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 5 \text{ A}$		6.9	8.5	11122	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 7 A		16		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1200		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		286			
Reverse Transfer Capacitance	C <sub>rss</sub>			190			
Total Gate Charge	Q <sub>q</sub>			16.5		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 7 \text{ A}$		1.3			
Gate-Drain Charge	Q <sub>gd</sub>			3.8			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		6		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			15		ns	
Rise Time	t <sub>r</sub>	V		10			
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD} = 10 \text{ V}, R_L = 1 \Omega$ $I_D \cong 7 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_\alpha = 1 \Omega$		13			
Fall Time	t <sub>f</sub>	D = 7 A, VGEN - 4.5 V, Ng - 132		10			
Turn-On Delay Time	t <sub>d(on)</sub>			11			
Rise Time	t <sub>r</sub>	V = -10 V B = 1 O		8			
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD} = 10 \text{ V}, R_L = 1 \Omega$ $I_D \cong 5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_a = 1 \Omega$		13			
Fall Time	t <sub>f</sub>			8		1	
<b>Drain-Source Body Diode Characteristic</b>	s						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			12	A	
Pulse Diode Forward Current	I <sub>SM</sub>				75	"	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V		0.6	1	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			20		ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 7 A, dl/dt = 100 A/μs, T <sub>J</sub> = 25 °C		8		nC	
Reverse Recovery Fall Time	t <sub>a</sub>	1 - 1 A, αναι – 100 Ανμδ, 1 J = 25 C		9		ne	
Reverse Recovery Rise Time	t <sub>b</sub>			10		ns	

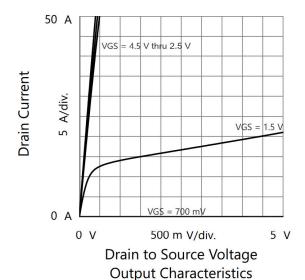
### Notes:

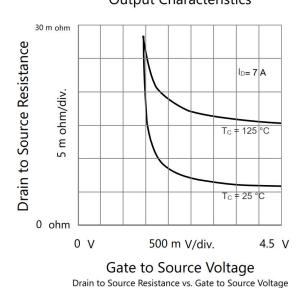
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

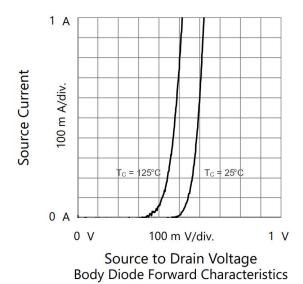
a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.

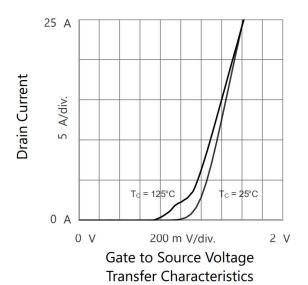


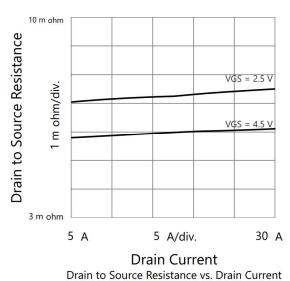
#### TYPICAL CHARACTERISTIC (25 °C, unless otherwise noted)

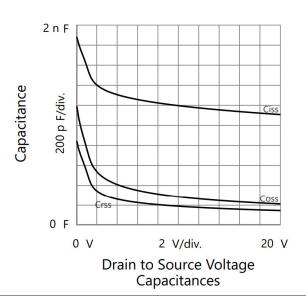












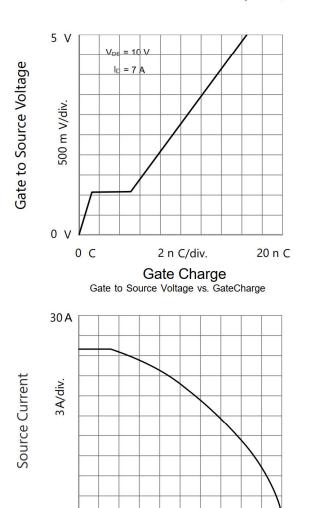




0 A

0 nC

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

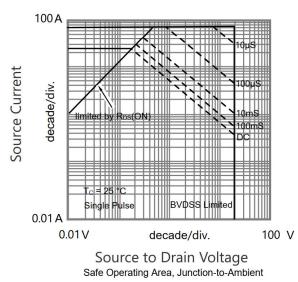


15 °C/div.

T<sub>C</sub> - Case Temperature

Current Derating

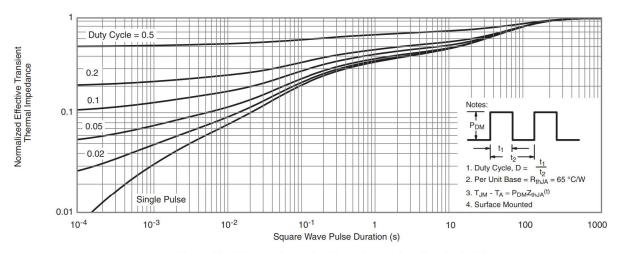
150 °C



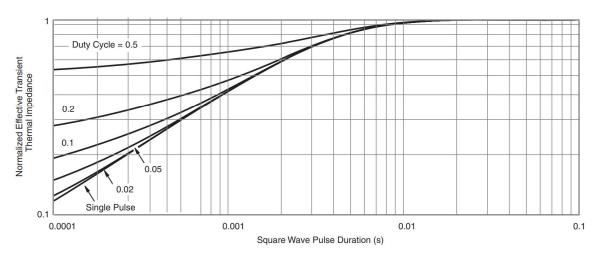
 $T_{C}$  - Case Temperature  $_{\text{Power Derating}}$ 



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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